



# SPN1022

## Dual N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN1022 is the Dual N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

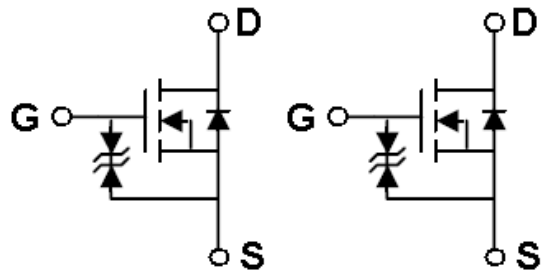
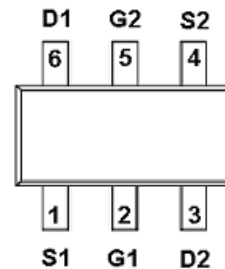
### FEATURES

- ◆ N-Channel  
20V/0.65A,  $R_{DS(ON)}=380m\Omega@V_{GS}=4.5V$   
20V/0.55A,  $R_{DS(ON)}=450m\Omega@V_{GS}=2.5V$   
20V/0.45A,  $R_{DS(ON)}=800m\Omega@V_{GS}=1.8V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-563 (SC-89-6L) package design

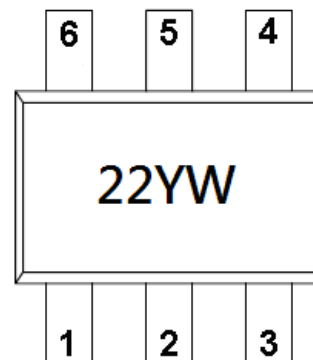
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION( SOT-563 / SC-89-6L)



### PART MARKING





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### PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	D2	Drain 2
4	S2	Source 2
5	G2	Gate 2
6	D1	Drain1

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN1022S56RGB	SOT-563	22

※ SPN1022S56RGB : Tape Reel ; Pb – Free, Halogen - Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	20	V	
Gate –Source Voltage	V <sub>GSS</sub>	±12	V	
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	TA=25°C	0.65	A
		TA=80°C	0.45	
Pulsed Drain Current	I <sub>DM</sub>	1.0	A	
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	0.3	A	
Power Dissipation	P <sub>D</sub>	TA=25°C	0.35	W
		TA=70°C	0.19	
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	



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### ELECTRICAL CHARACTERISTICS

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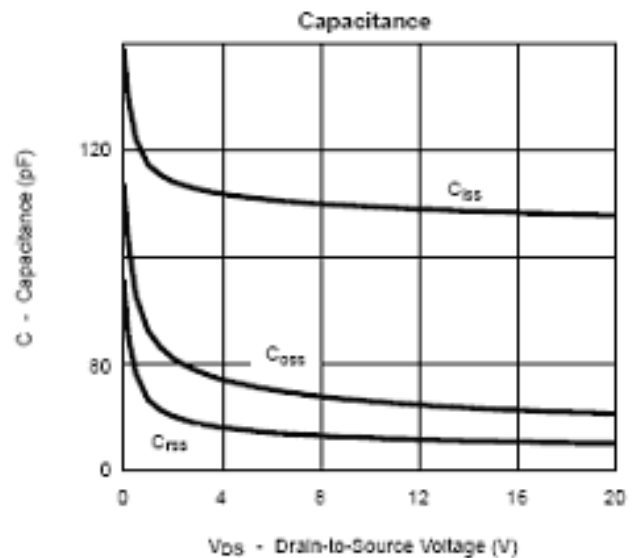
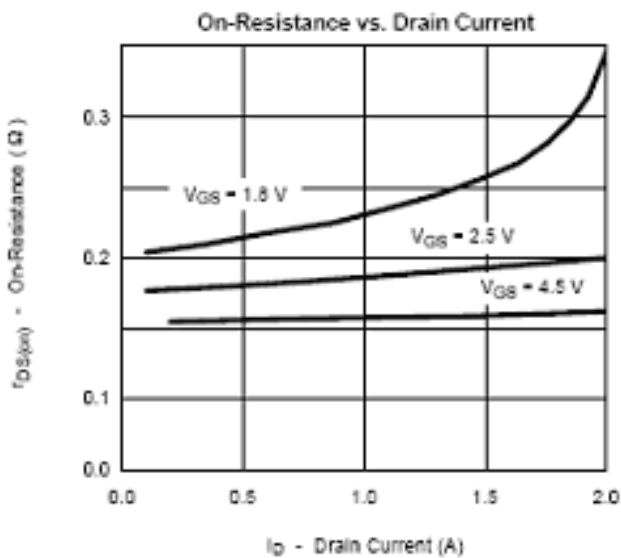
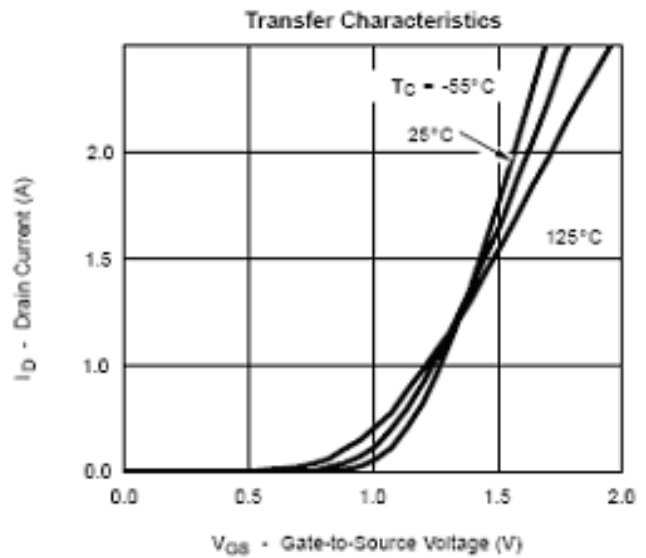
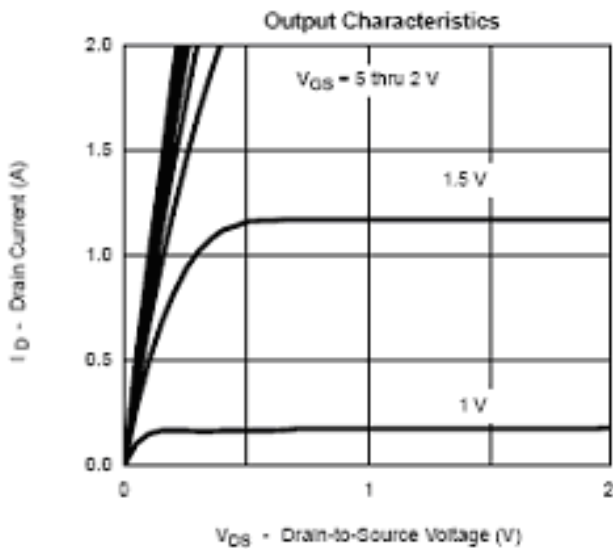
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.35		1.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			30	$\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=20V, V_{GS}=0V$ $T_J=55^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 4.5V, V_{GS}=5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.65A$		0.26	0.38	$\Omega$
		$V_{GS}=2.5V, I_D=0.55A$		0.32	0.45	
		$V_{GS}=1.8V, I_D=0.45A$		0.42	0.80	
Forward Transconductance	$g_{fs}$	$V_{DS}=10V, I_D=0.4A$		1.0		S
Diode Forward Voltage	$V_{SD}$	$I_S=0.15A, V_{GS}=0V$		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4.5V,$ $I_D=0.6A$		1.2	1.5	nC
Gate-Source Charge	$Q_{gs}$			0.2		
Gate-Drain Charge	$Q_{gd}$			0.3		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=10\Omega,$ $I_D=0.5A$ $V_{GEN}=4.5V, R_G=6\Omega$		5	10	ns
	$t_r$			8	15	
Turn-Off Time	$t_{d(off)}$			10	18	
	$t_f$			1.2	2.8	



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### TYPICAL CHARACTERISTICS

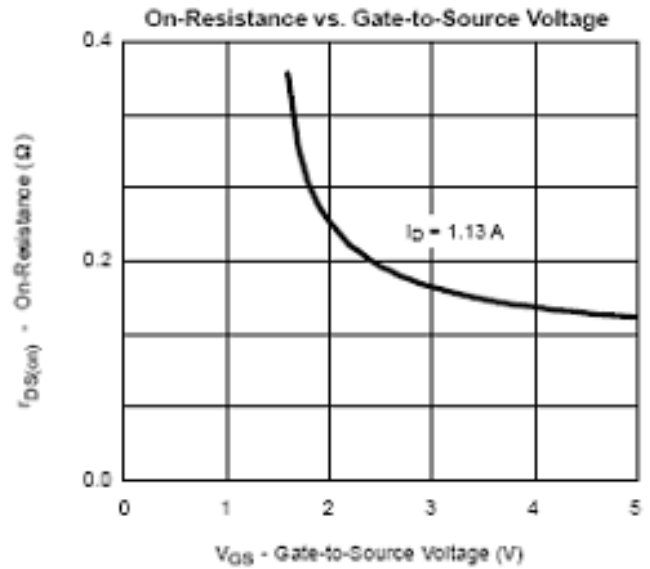
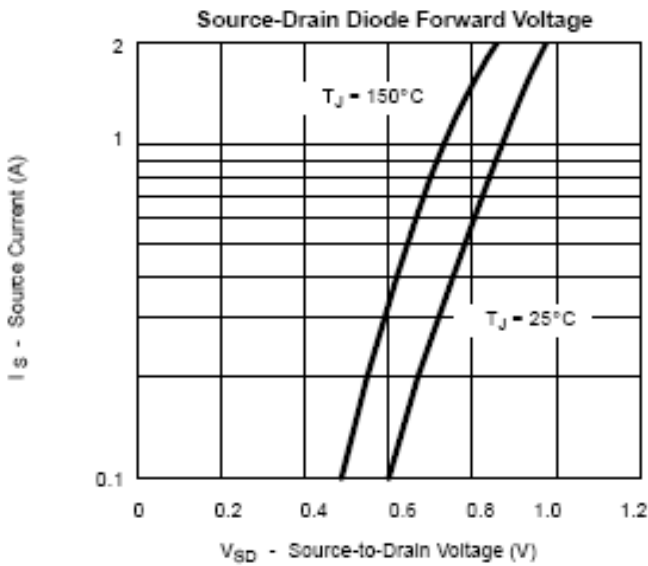
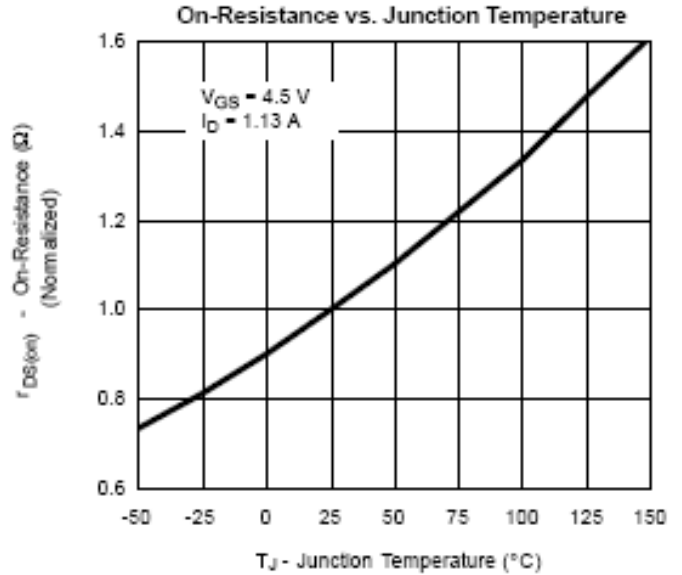
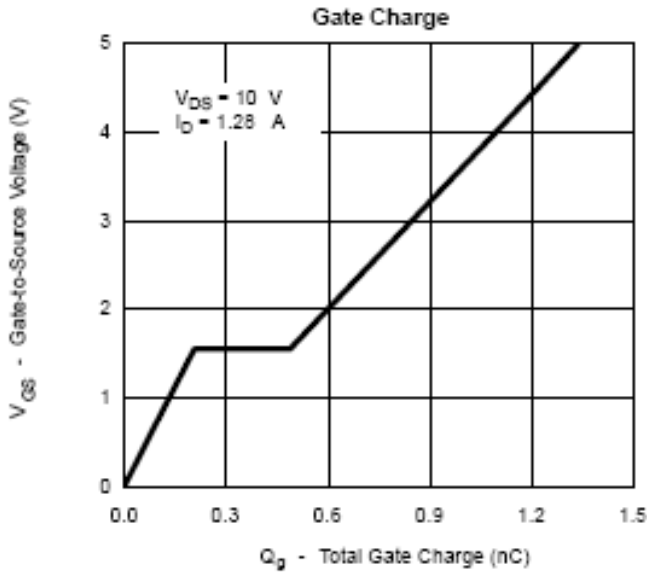




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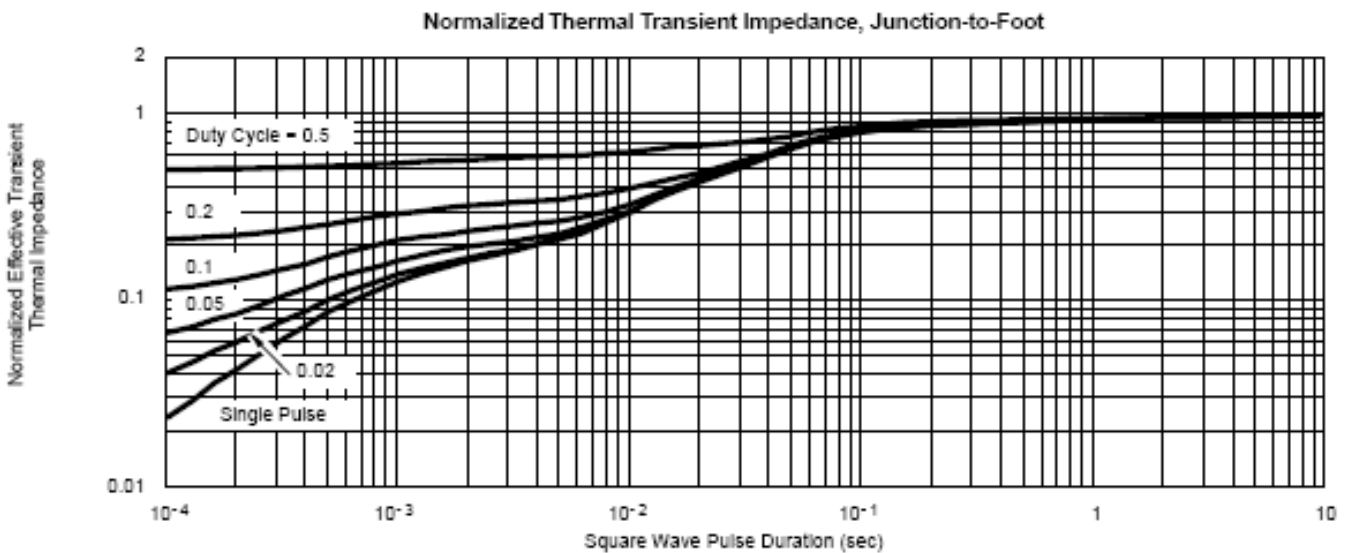
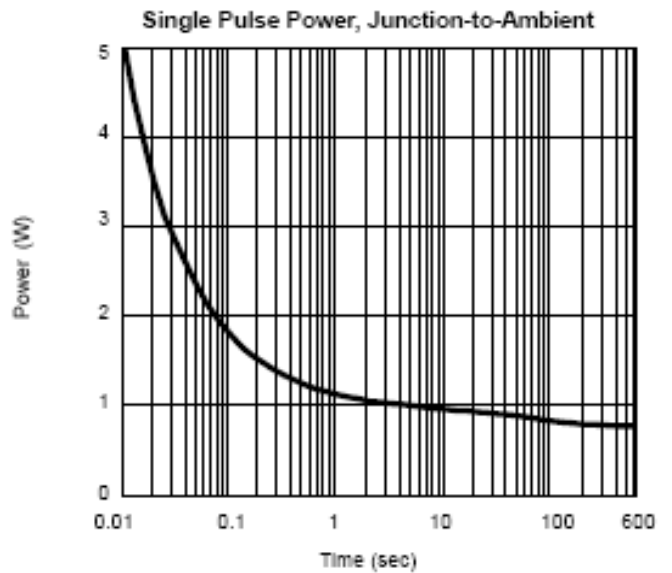
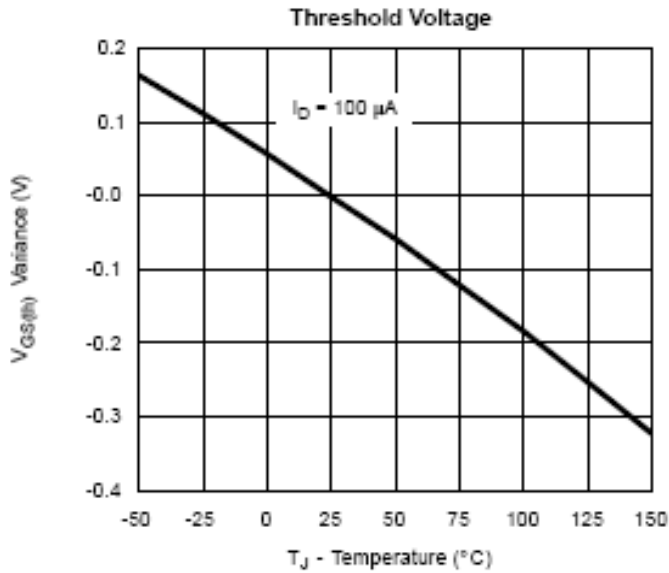




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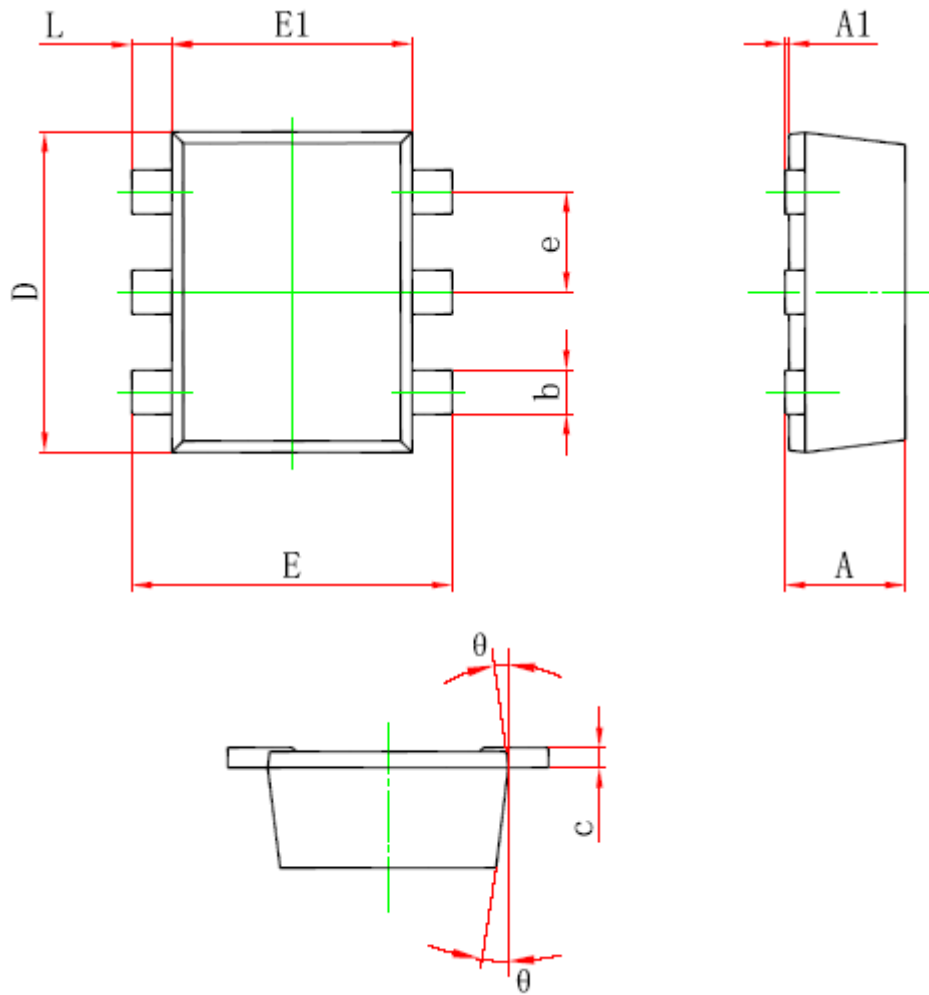




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### SOT-563 PACKAGE OUTLINE



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
θ	7° REF.		7° REF.	



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